Low-cost Si substrates from Si scraps and Si kerf: EU project Cabriss

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Si solar cell roadmap: low cost Si wafers/reduction of Si-content



Si substrates: Thin Si substrates < 100 µm; exfoliated Si foils; Si solar cells: HIT /MWT/EWT/IBC/BiFi solar cells

First generation PV: advanced concepts, lower Si content, kerf-less approaches, utilization of Si kerf, low-cost processing technologies,, are still required



Thin-film Si solar cells/reduction of Si-content

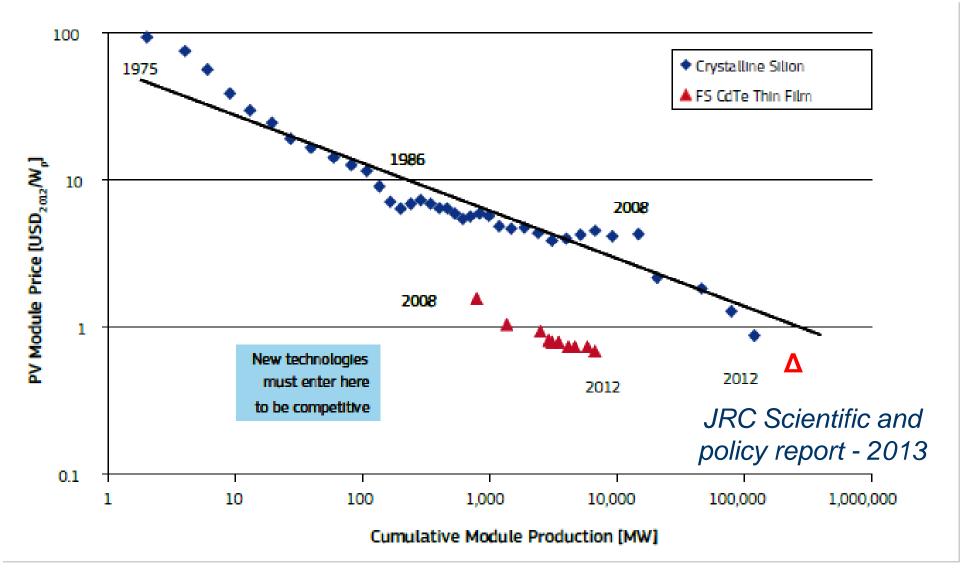
Epitaxial cells on low-cost substrates: 20–30 μ m

Polycrystalline Si cells grown at high temperatures or obtained by SPC, 3–10 μ m

a-Si:H \rightarrow microcrystalline Si / grown at temperatures < 300°C, 1 – 2 µm

Second generation PV, advanced concepts are still required, low-cost processing,







IMPLEMENTATION OF A CIRCULAR ECONOMY BASED ON RECYCLED,

REUSED AND RECOVERED INDIUM, SILICON AND SILVER MATERIALS

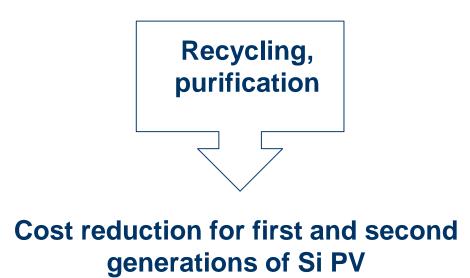
FOR PHOTOVOLTAIC AND OTHER APPLICATIONS





Recycling of Si /Si losses

- Si kerf ~ 50% loss of Si feedstock
- Si scrap: broken wafers, broken solar cells ~1-2% loss of Si
- **Extraction of Si from the end-of-life panels**





Recycling of Si

Si scrap: broken wafers, broken solar cells ~1-2% loss of Si

PV collection, selection and dismantling ...

Loser Chemie & PV Cycle

Materials extraction from Si PV waste Loser Chemie

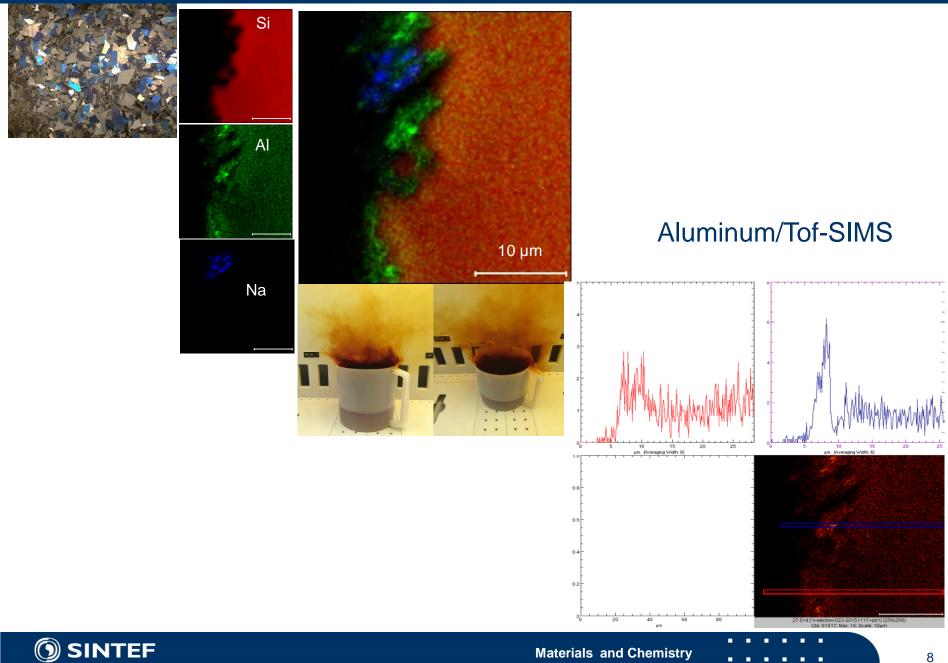
Example Si waste/Si scrap







Recycling of Si scrap



Recycling of Si /solar cells

G1 Multi-Si from Si scrap (Loser/SINT) shiped to THM for wafering



Solar cell processing at the Solitek industrial line

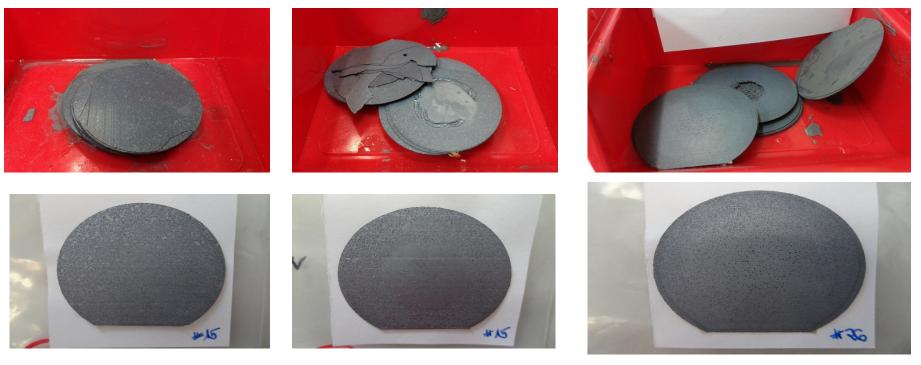
Title	Wafer count	Eta (%)	Voc (mV)	Jsc (mA/cm2)	FF(%)
Cabriss 4 (reference ingot from SINTEF)	78	17.24	627	34.7	79.19
Cabriss 6 (Si scrap)	37	17.26	625.3	35.3	78.18
Reference process at Solitek	1000	17.67	628	35.7	78.53
() SINTEF			Mate	rials and Chemistry	



Recycling of Si /Si powder based concept

Hot pressing/Spark plasma Si powder based wafers, 40 mm diameter (SINTEF) + wafering (THM)

Wafering of Si powder based sintered ingots is possible:



1200 °C

1250 °C

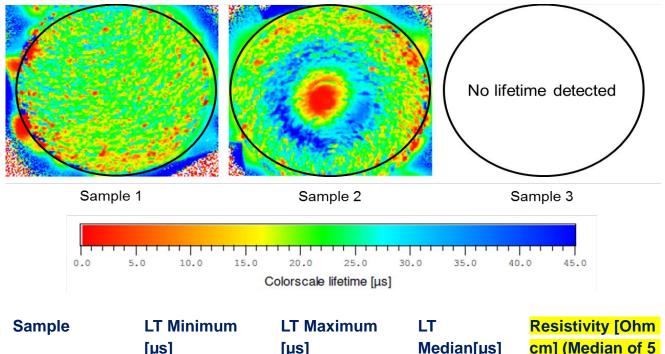
1200 °C



Recycling of Si /Si powder based concept

Minority carrier lifetime measurements at THM Undoped solar grade Si powder

p+ (Boron) Si powder



	[µs]	[µs]	Median[µs]	cm] (Median of 5
				measurements)
1	0.3	57.8	22.6	<mark>287.1</mark>
2	0.4	42.6	20.4	<mark>11.4</mark>
3	-	-	-	<mark>3.2x10⁻⁴</mark>



Recycling of Si /Si powder based concept

Ingot with 156mm x 156mm x 100 mm manufactured by direct hot pressing by RHP.

Wafering at THM (to be done)



Silicon and Boron doped Si-ingots



Recycling of Si /Si kerf

Si kerf- Resitec / Si ingots-SINTEF

Cabriss 1 (100% of Si kerf)



Cabriss 10 (5% of refined Si kerf)

Cabriss 2 (100% of Si kerf)



Cabriss 11 (100% of refined Si)

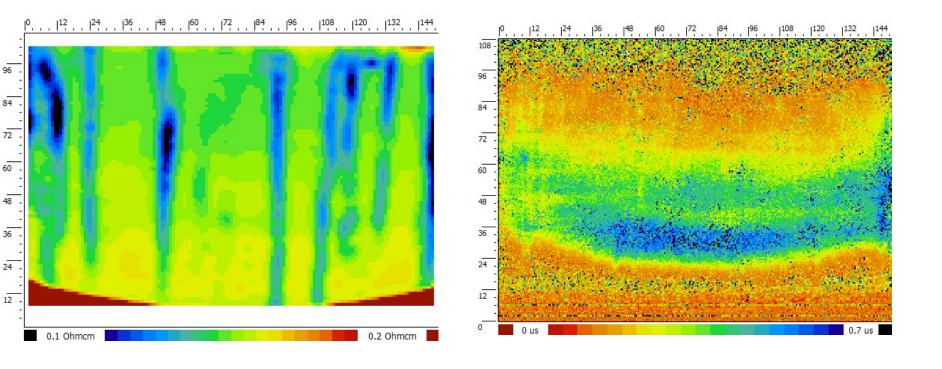






Recycling of Si /Si kerf

THM: Multicrystalline bricks CABRISS 10 : 5% of refined Si kerf • CABRISS 10: resistivity $0.1 - 0.2 \Omega$ cm • Carrier lifetime < 1 µs

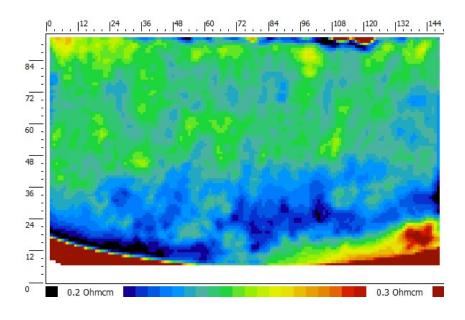




Recycling of Si /Si kerf

THM: Multicrystalline bricks CABRISS 11 (100% of refined Si kerf)

CABRISS 11: reistivity 0.2 – 0.3 Ωcm
No carrier lifetime detectable → resistivity is not the only reason for low lifetime, impurities must be present in high concentration

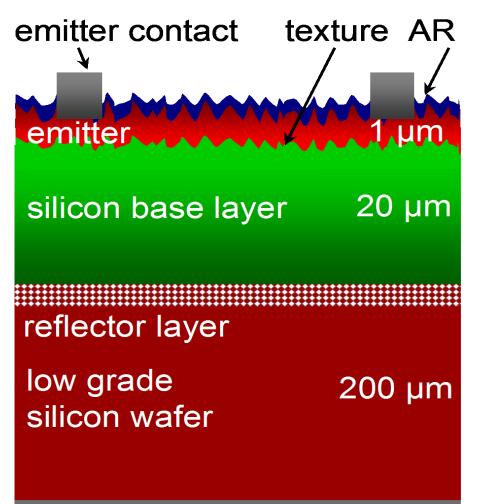




Wafering of Si kerf based ingots ??? THM



Si wafer equivalents /Si kerf/Si powder wafers/thermal spray of Si powders



Solar grade Si

Bonded Si foils (IMEC) Thermal spray of Si layers (Pyrogenesis) E-beam deposition (SINTEF) CVD ???

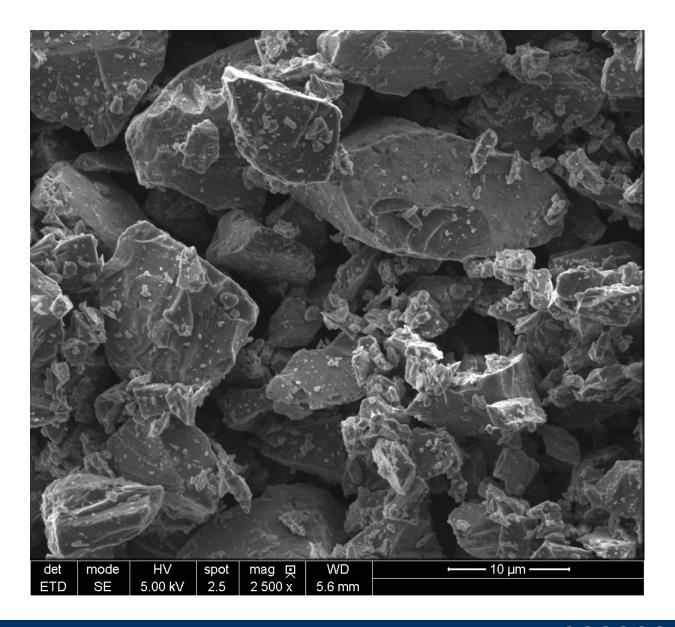
Low-cost/low grade Si

Si powder based substrates Si kerf based substrates Thermal spray based substrates

base contact



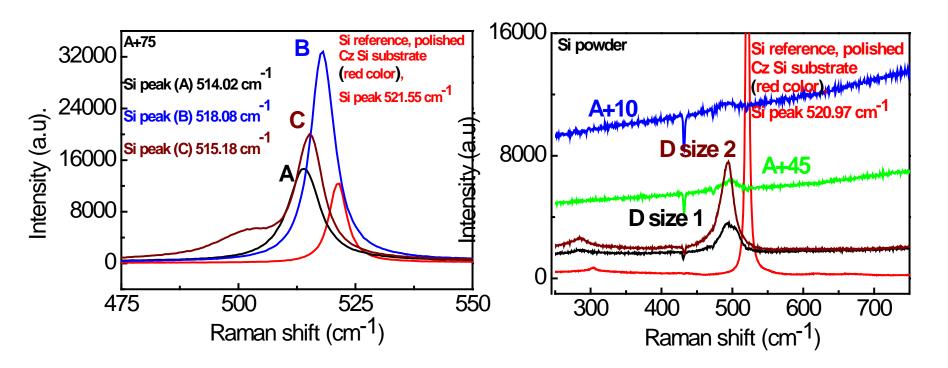
Si powder-to-substrate/layer approach/thermal spray





Mapping of individual Si particle

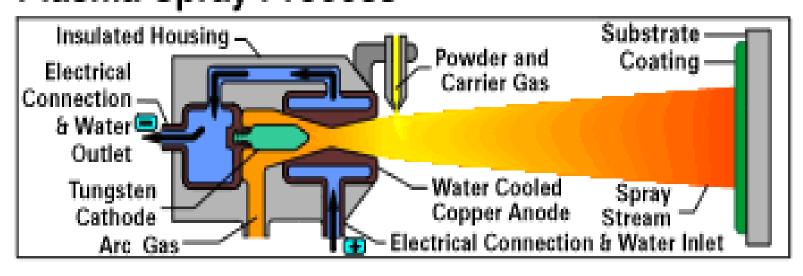
Different types of Si powder



Conclusion: Si powder sub-surface regions are not fully crystalline



Atmospheric Plasma Spray (APS) gun Plasma Spray Process







Si powder-to-substrate/layer approach/Pyrogenesis

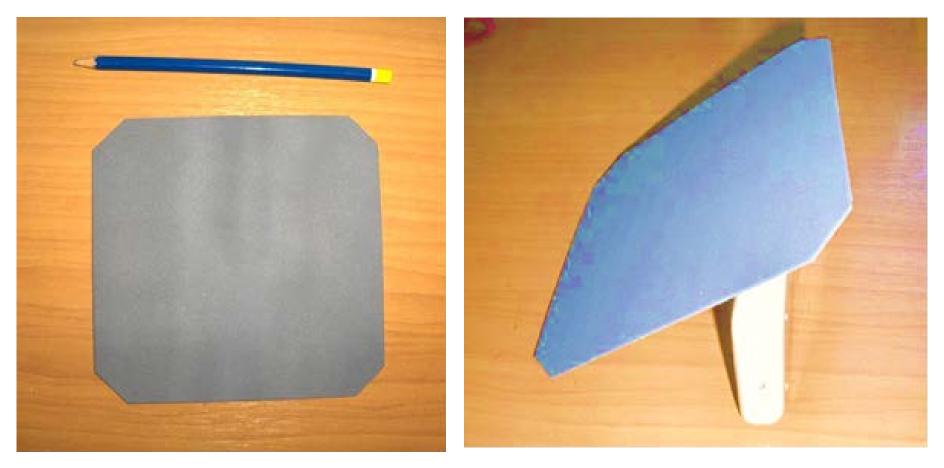
Low cost Si substrate made by TS with dimension 50x65 mm2





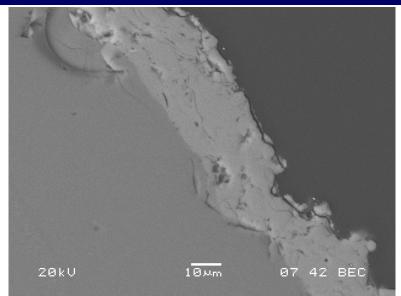
Si powder-to-substrate/layer approach/Pyrogenesis

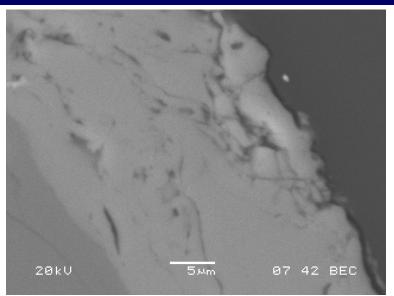
Low cost Si substrate made by TS with dimension 156x156 mm2

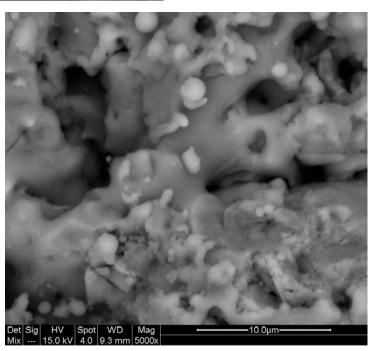




Si low cost layers on glass/ thermal spray/SEM





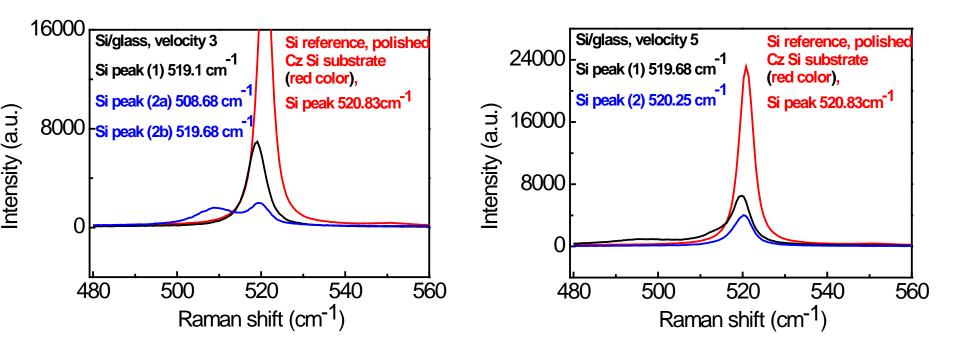


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Si low cost layers on glass/ thermal spray/Raman

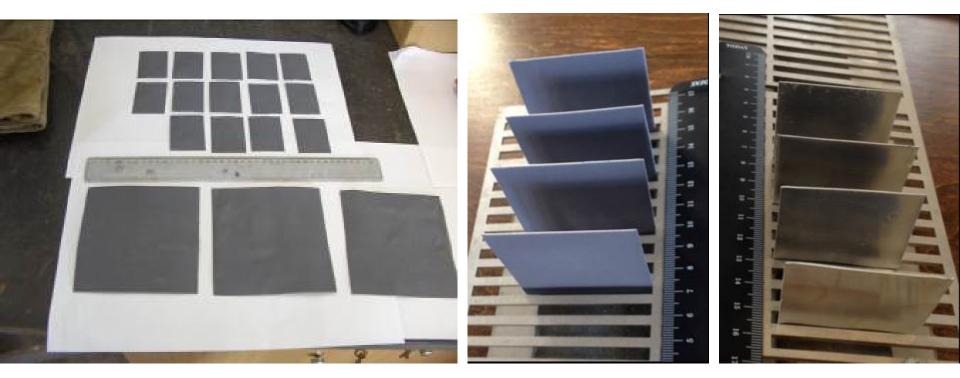
Thermal spray scanning velocity 3

Thermal spray scanning velocity 5





Thermal Spray of Si powder on Al foil





Thermal Spray of Si powder on ceramic roof tile/Pyrogenesis

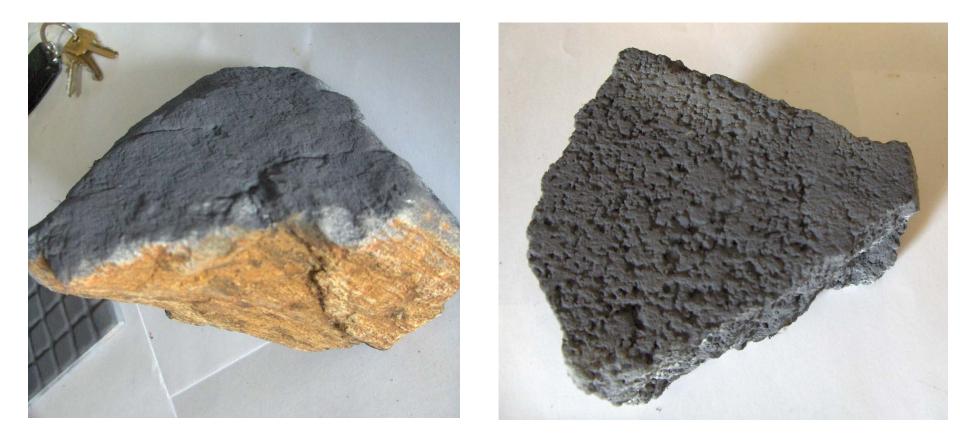




A ceramic roof tile, fully covered with Al/Si coatings



Thermal Spray of Si powder on natural stone and concrete



Si coating on natural stone

Si coating on concrete



Conclusions

- Recycled Si scrap can be used as a Si feedstock for Si PV (wafers/Si powder based layers)
- Refined Si kerf can be used for the growth of Si ingots
- Feasibility for wafering of Si kerf based ingots should be verified
- Si powder based ingots can be sintered from Si scrap based powders and can be wafered
- Feasibility to use sintered wafers for Si PV should be verified
- Thermal spray shows the potential for the in-situ low-temperature manufacturing of integrated c-Si layers on different substrates
- Low grade Si substrates can be used for the processing of Si wafer equivalents (at least via bonding of Si foils)



Thank you for your attention !

